

PMT29EN

30 V, 6 A N-channel Trench MOSFET

Rev. 1 — 31 August 2011

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT223 (SC-73) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Very fast switching

1.3 Applications

- Relay driver
- Low-side loadswitch
- High-speed line driver
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ }^{\circ}\text{C}$	-	-	30	V
V_{GS}	gate-source voltage		-20	-	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	6	A
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 6\text{ A}; T_j = 25\text{ }^{\circ}\text{C}$	-	24	29	m Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	SOT223 (SC-73)	017aaa253
2	D	drain		
3	S	source		
4	D	drain		



3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PMT29EN	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

4. Marking

Table 4. Marking codes

Type number	Marking code
PMT29EN	MT29EN

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

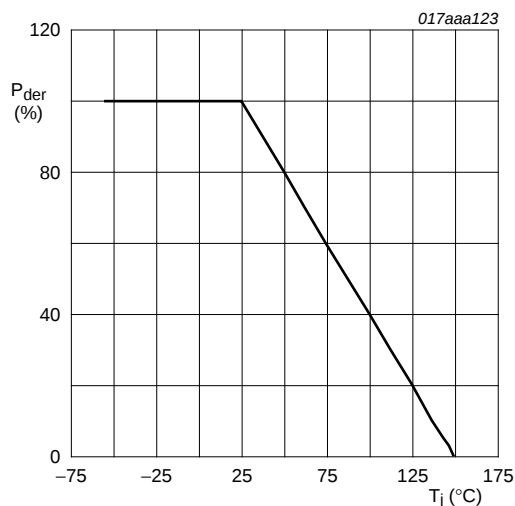
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ }^{\circ}\text{C}$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	6	A
		$V_{GS} = 10\text{ V}; T_{amb} = 100\text{ }^{\circ}\text{C}$	[1]	3.9	A
I_{DM}	peak drain current	$T_{amb} = 25\text{ }^{\circ}\text{C}$; single pulse; $t_p \leq 10\text{ }\mu\text{s}$	-	24	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ }^{\circ}\text{C}$	[2]	820	mW
			[1]	1760	mW
		$T_{sp} = 25\text{ }^{\circ}\text{C}$	-	8330	mW
T_j	junction temperature		-55	150	$^{\circ}\text{C}$
T_{amb}	ambient temperature		-55	150	$^{\circ}\text{C}$
T_{stg}	storage temperature		-65	150	$^{\circ}\text{C}$

Source-drain diode

I_S	source current	$T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	1.9	A
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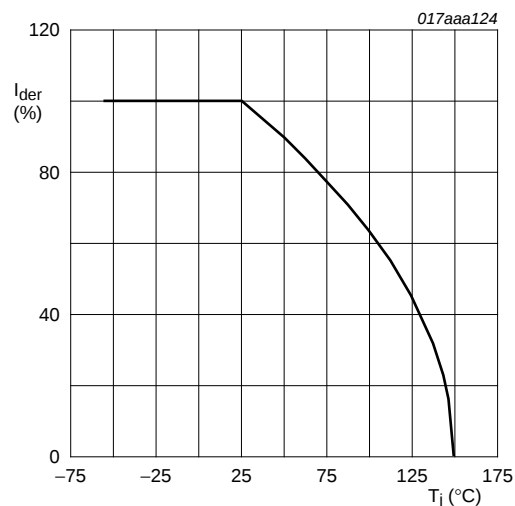
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



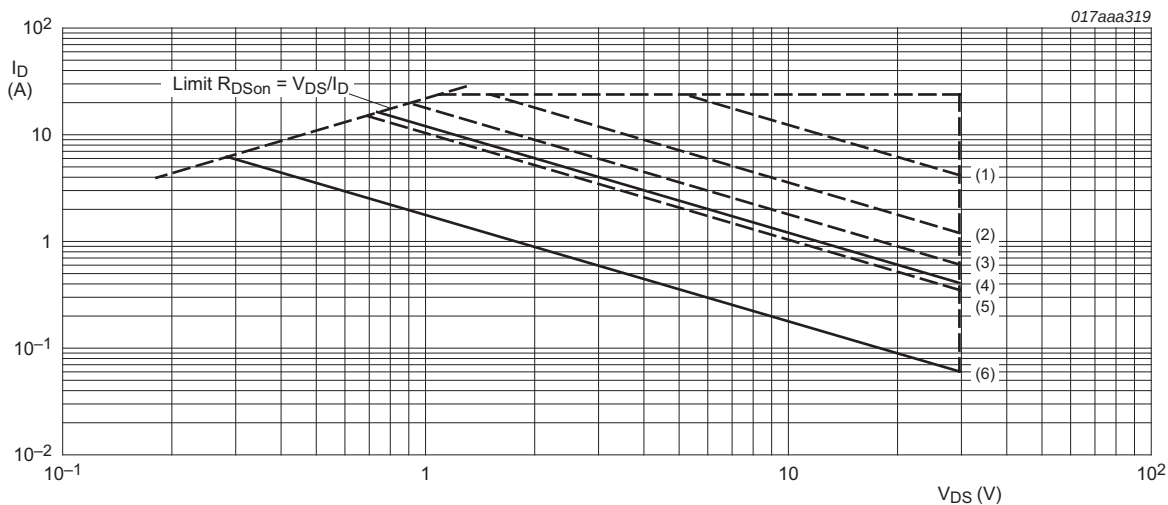
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of junction temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of junction temperature



IDM = single pulse
(1) tp = 100 μs
(2) tp = 1 ms
(3) tp = 10 ms
(4) DC; Tsp = 25 °C
(5) tp = 100 ms
(6) DC; Tamb = 25 °C; drain mounting pad 6 cm²

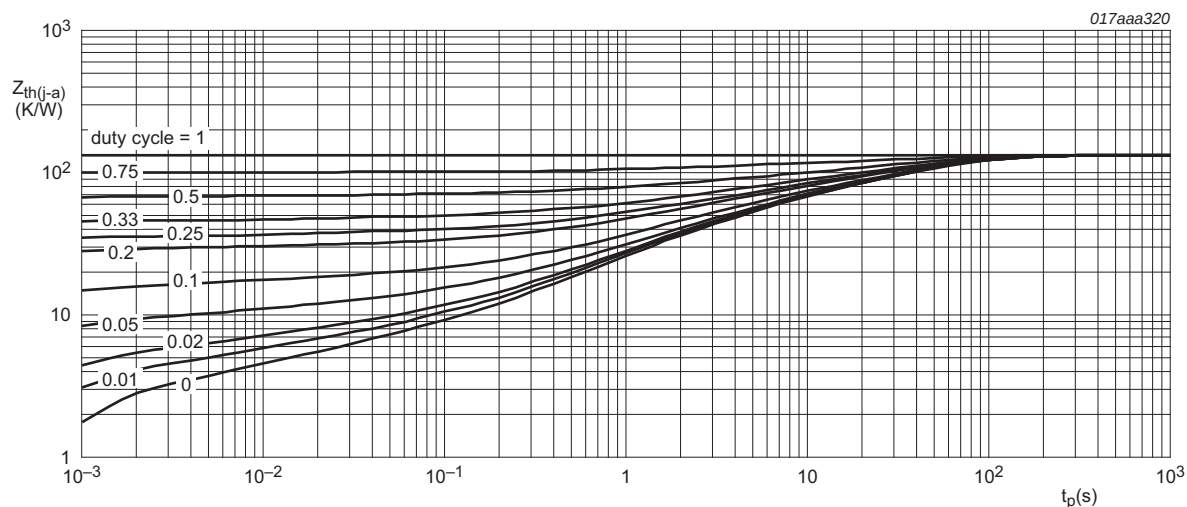
Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Rth(j-a)	thermal resistance from junction to ambient	in free air	[1]	-	131	K/W
			[2]	-	62	K/W
Rth(j-sp)	thermal resistance from junction to solder point		-	8	15	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

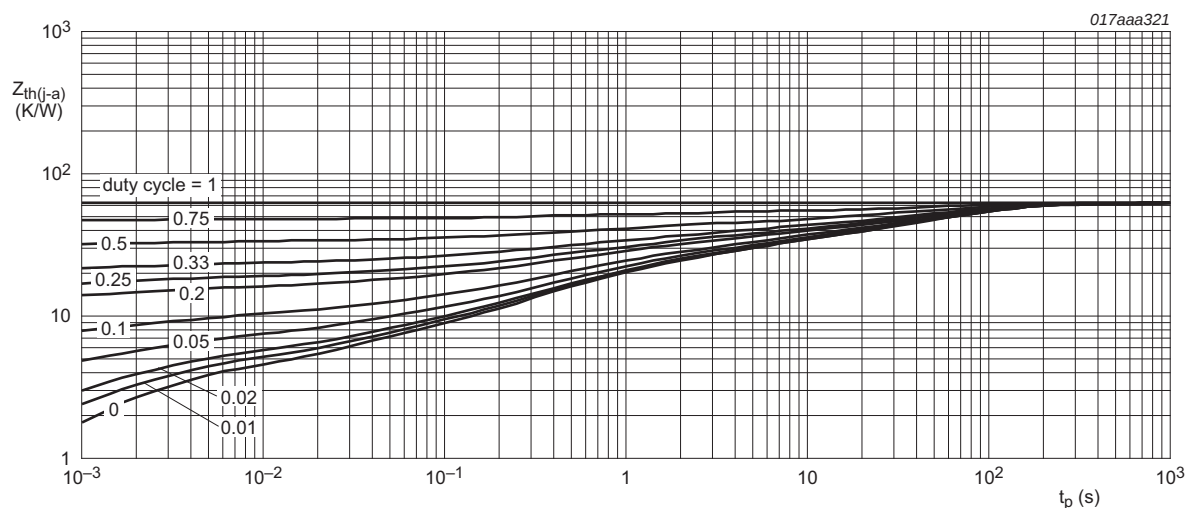
FR4 PCB, mounting pad for drain 6 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_j = 25 ^\circ C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 25 ^\circ C$	1	1.5	2.5	V
I_{DSS}	drain leakage current	$V_{DS} = 30 V$; $V_{GS} = 0 V$; $T_j = 25 ^\circ C$	-	-	1	μA
		$V_{DS} = 30 V$; $V_{GS} = 0 V$; $T_j = 150 ^\circ C$	-	-	10	μA

Table 7. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}$	-	-	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 6 \text{ A}; T_j = 25 \text{ }^{\circ}\text{C}$	-	24	29	m Ω
		$V_{GS} = 10 \text{ V}; I_D = 6 \text{ A}; T_j = 150 \text{ }^{\circ}\text{C}$	-	37	45	m Ω
		$V_{GS} = 4.5 \text{ V}; I_D = 5.1 \text{ A}; T_j = 25 \text{ }^{\circ}\text{C}$	-	29	36	m Ω
g_{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 6 \text{ A}; T_j = 25 \text{ }^{\circ}\text{C}$	-	18	-	S

Dynamic characteristics

$Q_{G(tot)}$	total gate charge	$V_{DS} = 15 \text{ V}; I_D = 6 \text{ A}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}$	-	9.6	11	nC
Q_{GS}	gate-source charge		-	1.5	-	nC
Q_{GD}	gate-drain charge		-	1.5	-	nC
C_{iss}	input capacitance	$V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}$	-	492	-	pF
C_{oss}	output capacitance		-	115	-	pF
C_{rss}	reverse transfer capacitance		-	54	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V}; R_{G(ext)} = 6 \text{ } \Omega; T_j = 25 \text{ }^{\circ}\text{C}; I_D = 6 \text{ A}$	-	5	-	ns
t_r	rise time		-	28	-	ns
$t_{d(off)}$	turn-off delay time		-	94	-	ns
t_f	fall time		-	40	-	ns

Source-drain diode

V_{SD}	source-drain voltage	$I_S = 1.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^{\circ}\text{C}$	-	0.8	1.2	V
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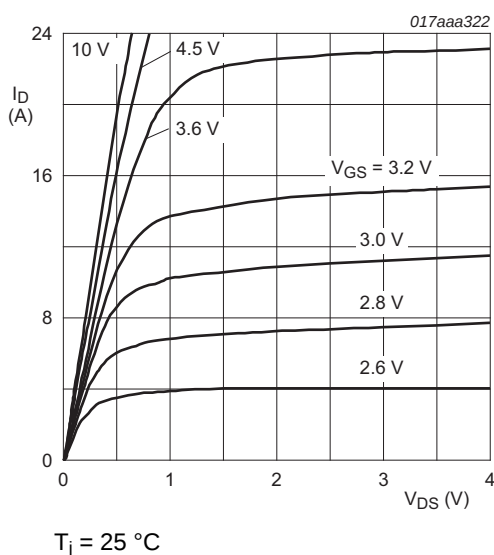
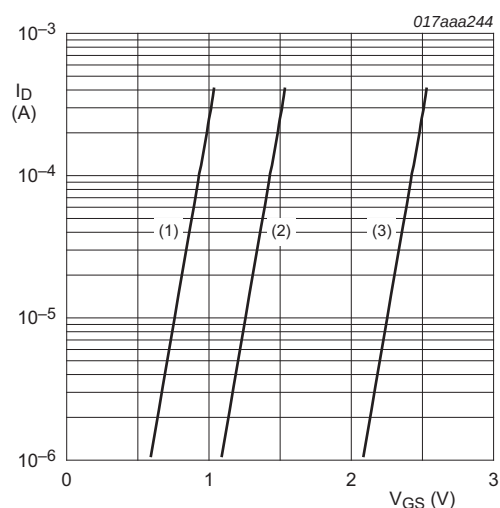
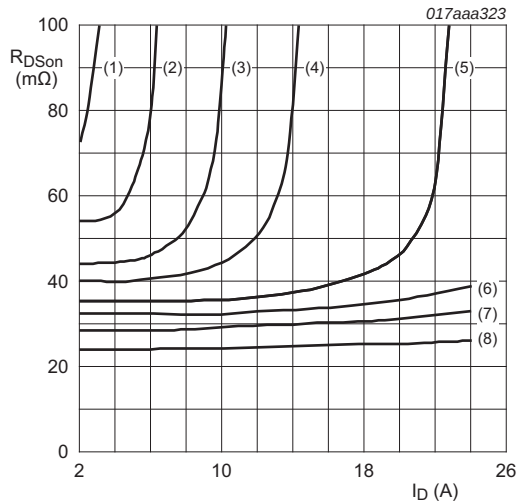


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$T_j = 25 \text{ }^{\circ}\text{C}; V_{DS} = 5 \text{ V}$
 (1) minimum values
 (2) typical values
 (3) maximum values

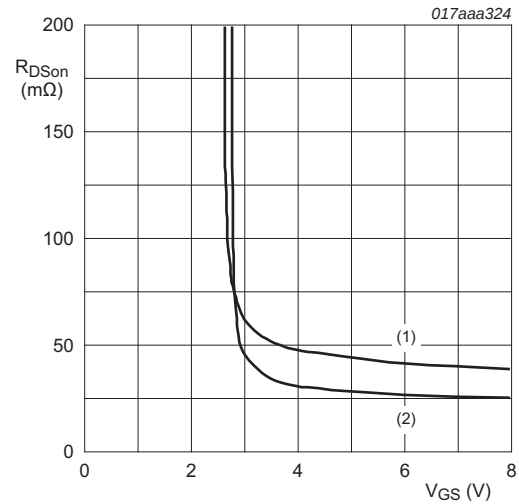
Fig 7. Sub-threshold drain current as a function of gate-source voltage



$T_j = 25\text{ °C}$

- (1) $V_{GS} = 2.6\text{ V}$
- (2) $V_{GS} = 2.8\text{ V}$
- (3) $V_{GS} = 3.0\text{ V}$
- (4) $V_{GS} = 3.2\text{ V}$
- (5) $V_{GS} = 3.6\text{ V}$
- (6) $V_{GS} = 4.0\text{ V}$
- (7) $V_{GS} = 4.5\text{ V}$
- (8) $V_{GS} = 10.0\text{ V}$

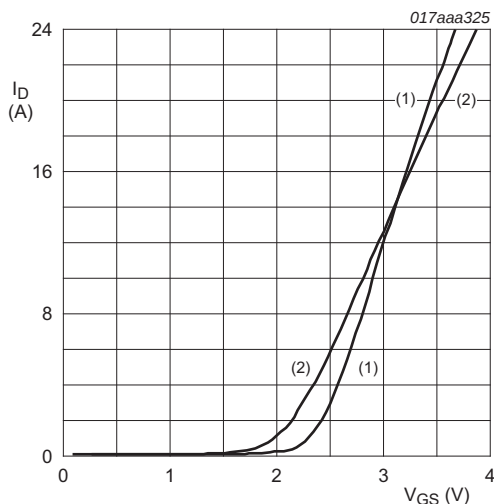
Fig 8. Drain-source on-state resistance as a function of drain current; typical values



$I_D = 6\text{ A}$

- (1) $T_j = 150\text{ °C}$
- (2) $T_j = 25\text{ °C}$

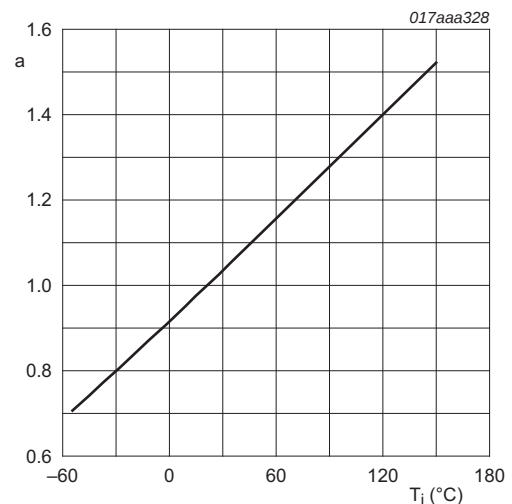
Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



$V_{DS} > I_D \times R_{DS(on)}$

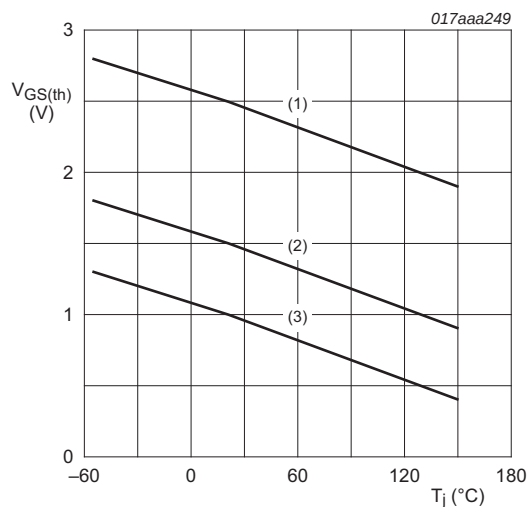
- (1) $T_j = 25\text{ °C}$
- (2) $T_j = 150\text{ °C}$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



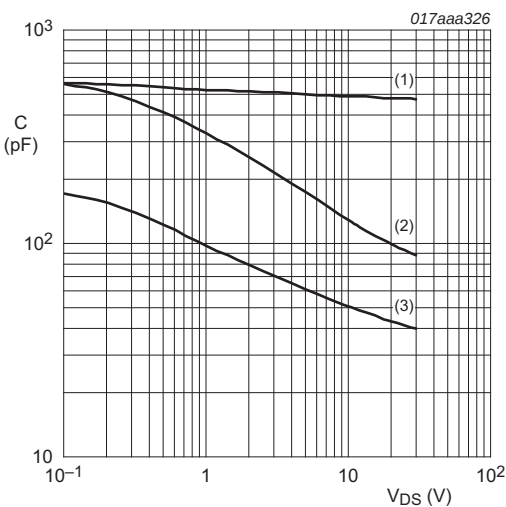
$$a = \frac{R_{DS(on)}}{R_{DS(on)}(25\text{ °C})}$$

Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



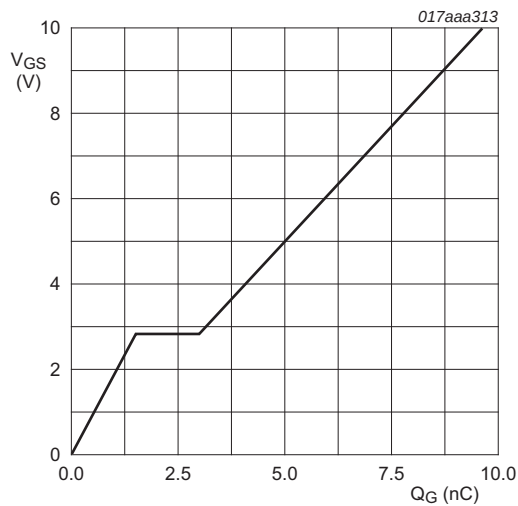
$I_D = 0.25\text{ mA}$; $V_{DS} = V_{GS}$
(1) maximum values
(2) typical values
(3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



$f = 1\text{ MHz}$; $V_{GS} = 0\text{ V}$
(1) C_{iss}
(2) C_{oss}
(3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 6\text{ A}$; $V_{DS} = 10\text{ V}$; $T_{amb} = 25\text{ °C}$

Fig 14. Gate-source voltage as a function of gate charge; typical values

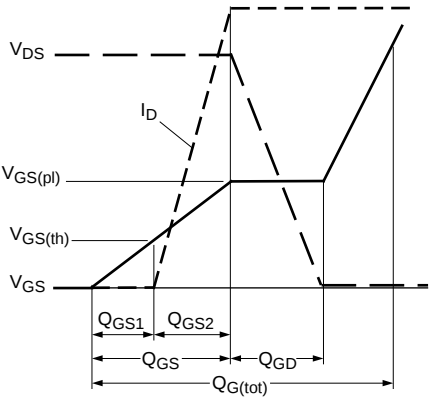
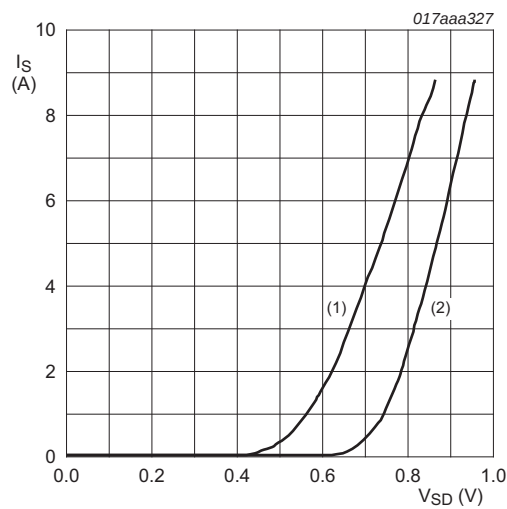


Fig 15. Gate charge waveform definitions



$V_{GS} = 0\text{ V}$
(1) $T_j = 150\text{ }^{\circ}\text{C}$
(2) $T_j = 25\text{ }^{\circ}\text{C}$

Fig 16. Source current as a function of source-drain voltage; typical values

8. Test information

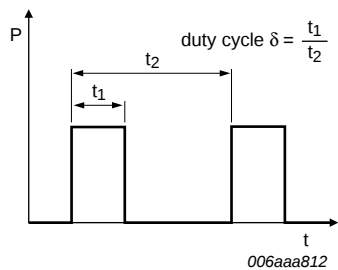


Fig 17. Duty cycle definition

9. Package outline

Plastic surface-mounted package with increased heatsink; 4 leads SOT223

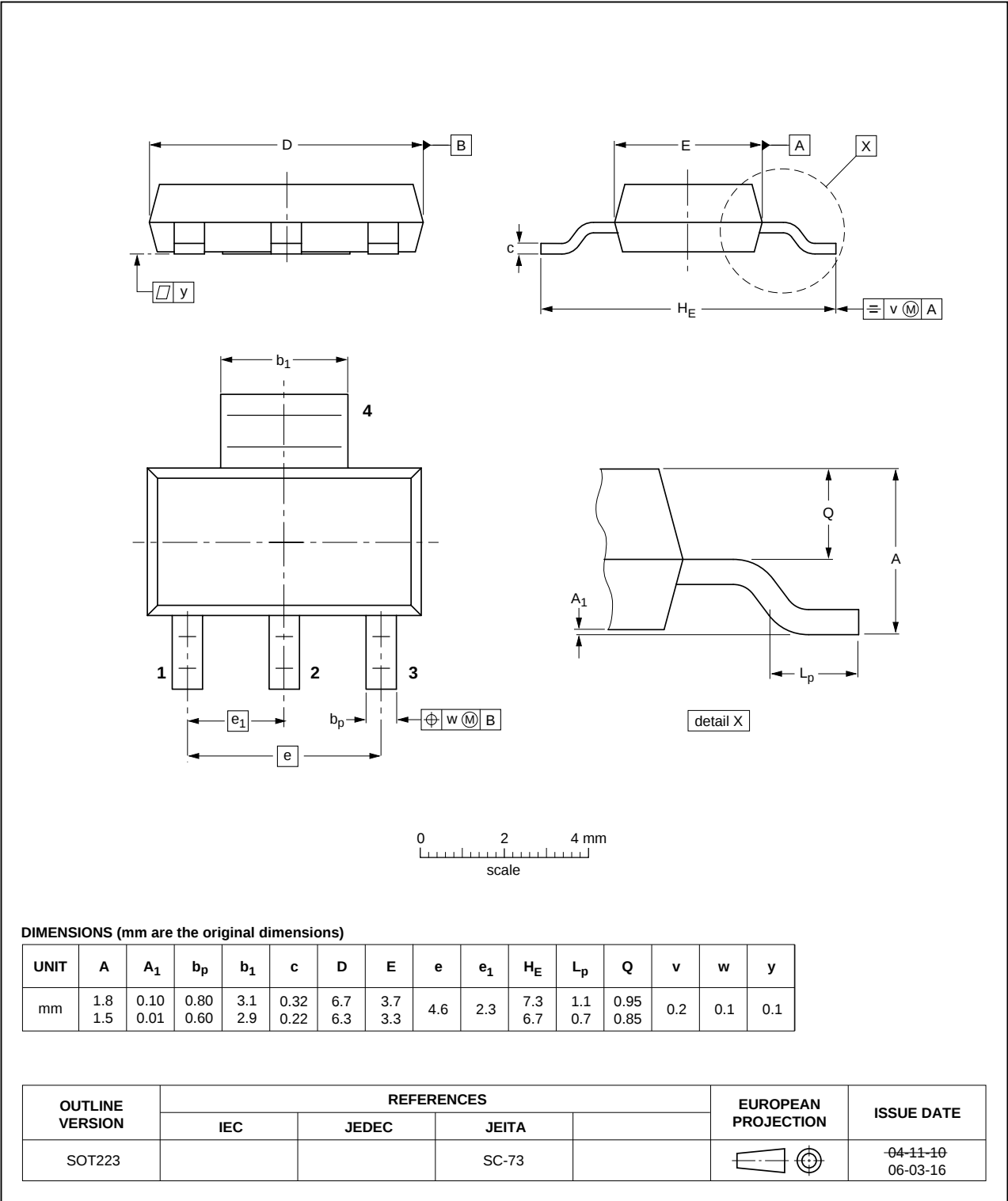


Fig 18. Package outline SOT223 (SC-73)

10. Soldering

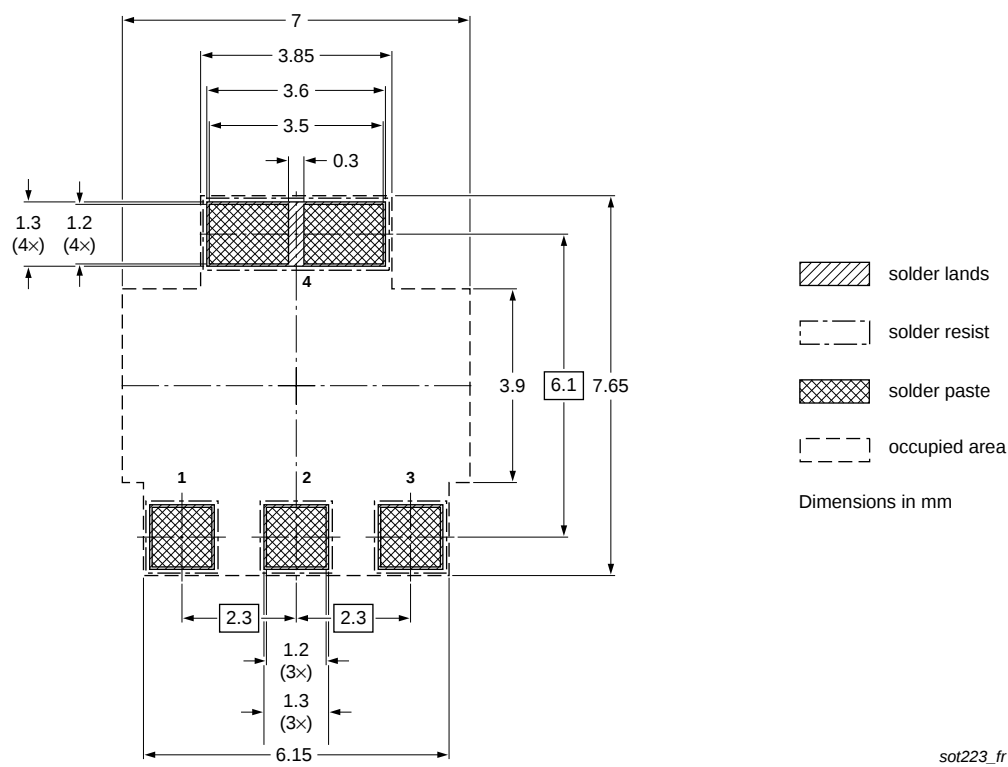


Fig 19. Reflow soldering footprint for SOT223 (SC-73)

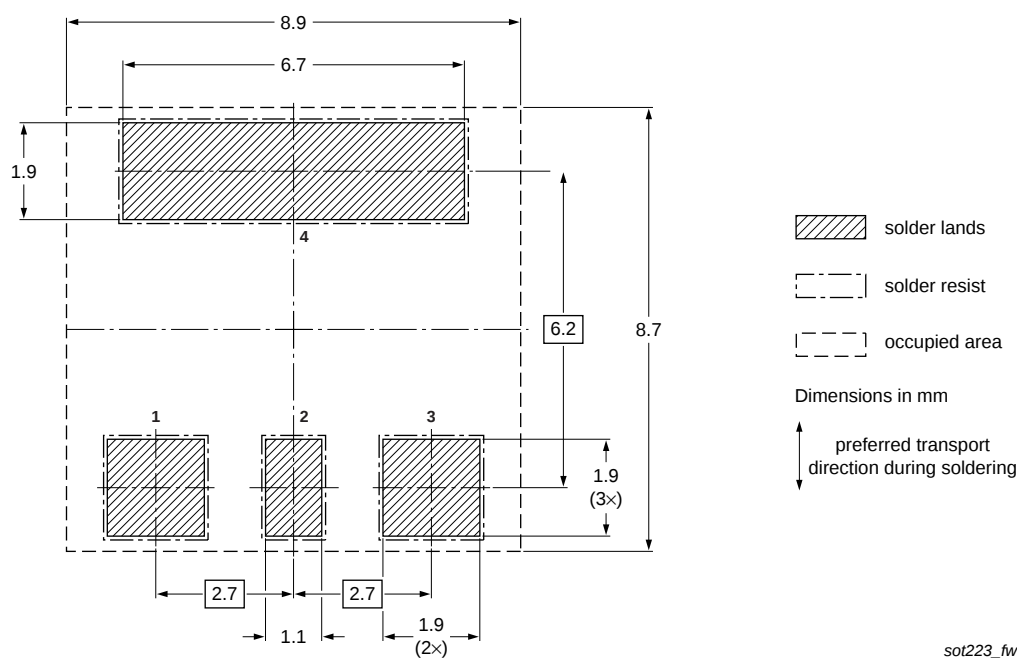


Fig 20. Wave soldering footprint for SOT223 (SC-73)

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMT29EN v.1	20110831	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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